

/ Descriptions

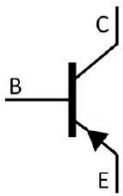
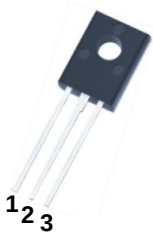
Silicon PNP transistor in a TO-126F Plastic Package.

/ Features

Complement to BD135.

/ Applications

Medium power linear and switching applications.

/ Equivalent Circuit**/ Pinning**

PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	6	10	16
h_{FE} Range	40 100	63 160	100 250

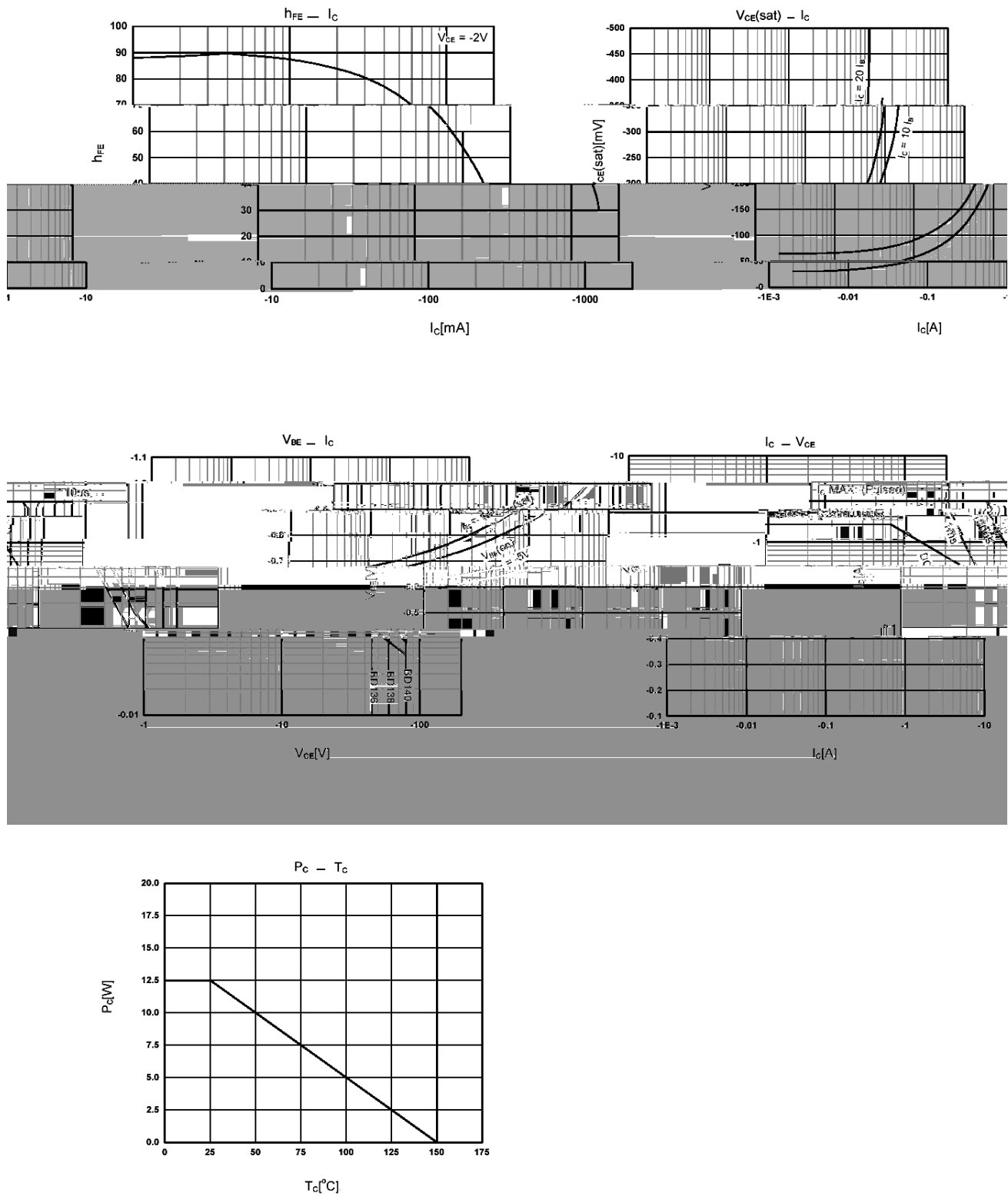
/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-45	V
Collector to Emitter Voltage	V_{CEO}	-45	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-1.5	A
Collector Current – Continuous	I_{CP}	-3.0	A
Base Current – Continuous	I_B	-0.5	A
Collector Power Dissipation	P_C	1.25	W
Collector Power Dissipation	$P_C(T_c=25^{\circ}C)$	12.5	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}C$

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-30mA$ $I_B=0$	-45			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30V$ $I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-10	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2.0V$ $I_C=-150mA$	40		250	
	$h_{FE(2)}$	$V_{CE}=-2.0V$ $I_C=-500mA$	25			
	$h_{FE(3)}$	$V_{CE}=-2.0V$ $I_C=-5.0mA$	25			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA$ $I_B=-50mA$			-0.5	V
Base to Emitter On Voltage	$V_{BE(on)}$	$V_{CE}=-2.0V$ $I_C=-500mA$			-1.0	V

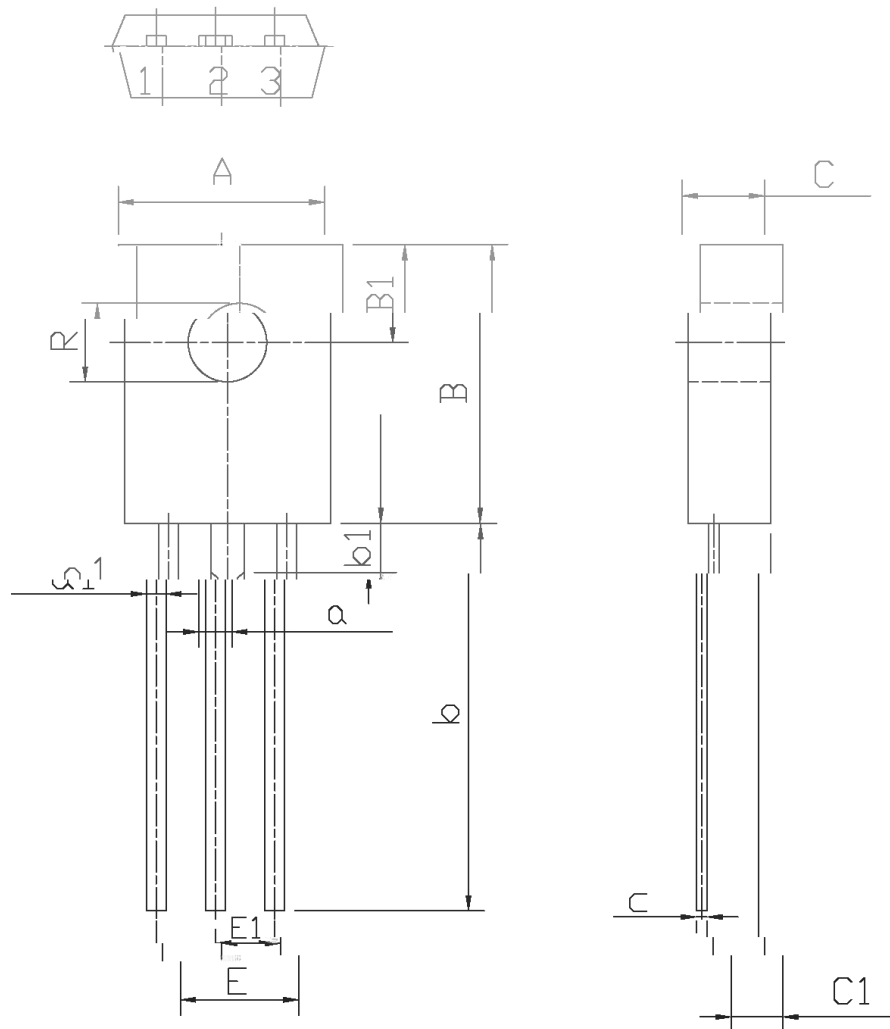
/ Electrical Characteristic Curve



/ Package Dimensions

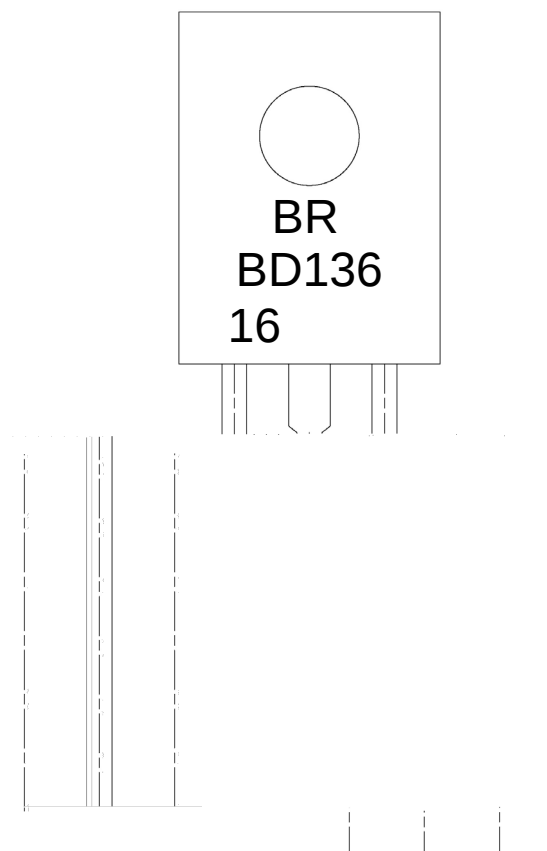
TU-126

单位: mm



Symbol	Dimensions in Millimeters		Symbol	Dimensions in Millimeters	
	Min	Max		Min	Max
A	7.8	8.2	a1	0.55	0.85
B	10.8	11.2	E	4.4	4.8
B1	3.8	4.2	C	3.1	3.3
R	2.95	3.15	C1	1.9	2.1
b	14	16	c	0.3	0.6
b1	1.9		a	1.27	
E1	2.1	2.5			

/ Marking Instructions



Note:

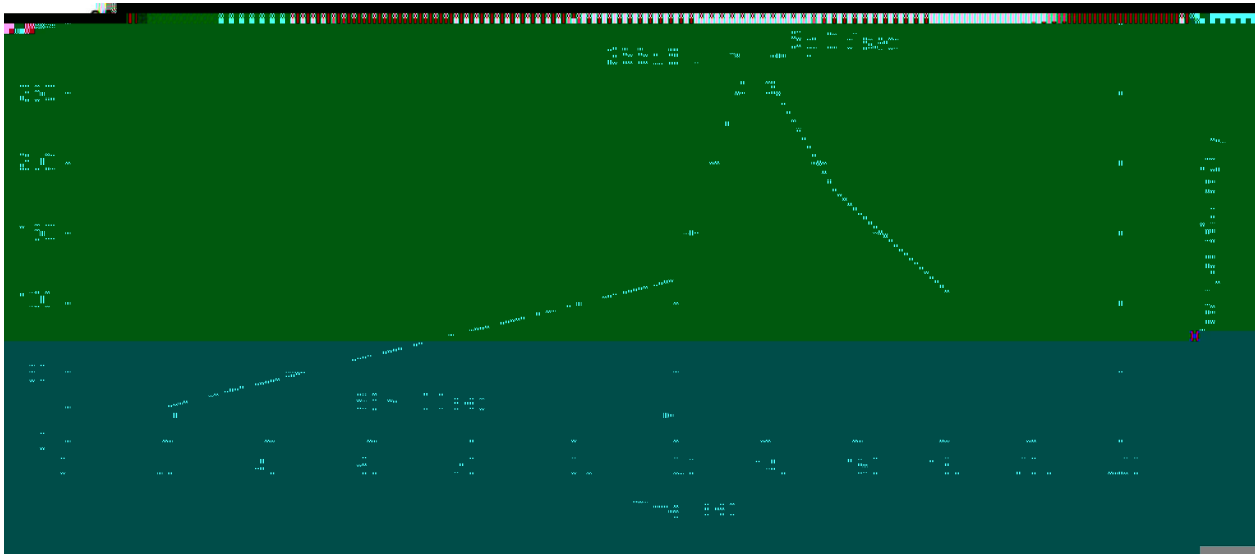
BR: Company Code

BD136: Product Type.

16: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270 5

10 1 sec.

Temp.:270±5℃

Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units	Dimension	(unit mm ³)
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